

MOSFETs Silicon N-Channel MOS (DTMOS V)

TK290A60Y

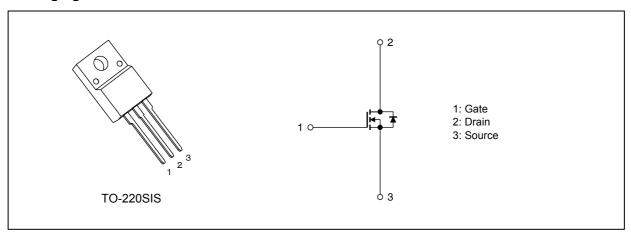
1. Applications

· Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.23 \Omega$ (typ.) by using Super Junction Structure: DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: $V_{th} = 3$ to $4 \text{ V} (V_{DS} = 10 \text{ V}, I_D = 0.45 \text{mA})$

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Character | Symbol | Rating | Unit | | |
|--------------------------------|---------------------------|----------|-----------------------|------------|-------|
| Drain-source voltage | | | V _{DSS} | 600 | V |
| Gate-source voltage | | | V _{GSS} | ±30 | |
| Drain current (DC) | (T _c = 25 °C) | (Note 1) | I _D | 11.5 | Α |
| Drain current (DC) | (T _c = 100 °C) | (Note 1) | I _D | 7.3 | Α |
| Drain current (pulsed) | (T _c = 25 °C) | (Note 1) | I _{DP} | 46 | Α |
| Power dissipation | (T _c = 25 °C) | | P _D | 35 | W |
| Single-pulse avalanche energy | | (Note 2) | E _{AS} | 114 | mJ |
| Single-pulse avalanche current | | | I _{AS} | 3 | Α |
| Reverse drain current (DC) | | (Note 1) | I _{DR} | 11.5 | |
| Reverse drain current (pulsed) | | (Note 1) | I _{DRP} | 46 | Α |
| Channel temperature | | | T _{ch} | 150 | °C |
| Storage temperature | | | T _{stg} | -55 to 150 | °C |
| Isolation voltage (RMS) | (t = 1.0 s) | | V _{ISO(RMS)} | 2000 | V |
| Mounting torque | | | TOR | 0.6 | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2016-12



5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 3.57 | °C/W |
| Channel-to-ambient thermal resistance | R _{th(ch-a)} | 62.5 | |

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 22.3 mH, R_G = 25 Ω , I_{AS} = 3 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±1 | μΑ |
| Drain cut-off current | I _{DSS} | V _{DS} = 600 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 600 | _ | _ | V |
| Gate threshold voltage | V_{th} | V _{DS} = 10 V, I _D = 0.45 mA | 3 | _ | 4 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 10 V, I _D = 5.8 A | _ | 0.23 | 0.29 | Ω |

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|--------------------|---|-----|------|-----|------|
| Input capacitance | C _{iss} | $V_{DS} = 300 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}$ | _ | 730 | _ | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 2.5 | _ | |
| Output capacitance | C _{oss} | | _ | 26 | _ | |
| Effective output capacitance | C _{o(er)} | V _{DS} = 0 to 400 V, V _{GS} = 0 V | _ | 48 | _ | |
| Gate resistance | r _g | V _{DS} = OPEN , f = 1 MHz | _ | 32 | _ | Ω |
| Switching time (rise time) | t _r | See Figure 6.2.1 | _ | 25 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 65 | _ | |
| Switching time (fall time) | t _f | | _ | 8.5 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 170 | _ | |
| MOSFET dv/dt ruggedness | dv/dt | $V_{DS} \le V_{(BR)DSS}$, $I_D \le 5.8 A$ | 50 | _ | _ | V/ns |

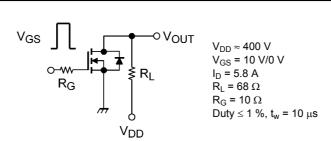


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Q_g | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 11.5 \text{ A}$ | | 25 | | nC |
| Gate-source charge 1 | Q _{gs1} | | | 4 | _ | |
| Gate-drain charge | Q_{gd} | | | 13 | | |

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|-----------------|--|-----|------|------|------|
| Diode forward voltage | V_{DSF} | I _{DR} = 11.5 A, V _{GS} = 0 V | _ | _ | -1.7 | V |
| Reverse recovery time | t _{rr} | V _{DD} ≈ 400 V | _ | 240 | _ | ns |
| Reverse recovery charge | Q_{rr} | I_{DR} = 5.8 A, V_{GS} = 0 V -d I_{DR} /dt = 100 A/ μ s | _ | 2.3 | _ | μС |
| Peak reverse recovery current | I _{rr} | -αιρκ/αι – 100 Α/μο | _ | 20 | _ | Α |
| Diode dv/dt ruggedness | dv/dt | $V_{DS} \le 400 \text{ V}, I_{DR} \le 5.8 \text{ A}, V_{GS} = 0 \text{ V}$ | 15 | _ | _ | V/ns |



7. Marking (Note)

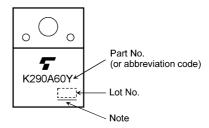


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

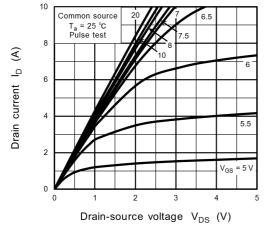
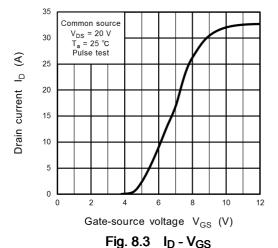


Fig. 8.1 I_D - V_{DS}



Drain-source voltage V_{DSS} 600 550 500 L -100

Ambient temperature T_a (°C) Fig. 8.5 V_{DSS} - T_a

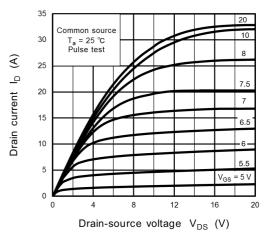


Fig. 8.2 I_D - V_{DS}

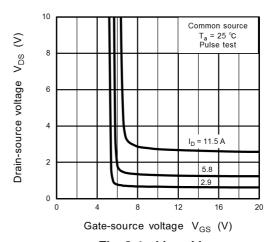


Fig. 8.4 V_{DS} - V_{GS}

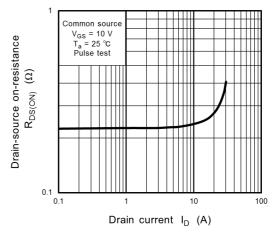


Fig. 8.6 R_{DS(ON)} - I_D

700

650

 \leq

Common source $V_{GS} = 0 \text{ V}$ $I_D = 10 \text{ mA}$ Pulse test

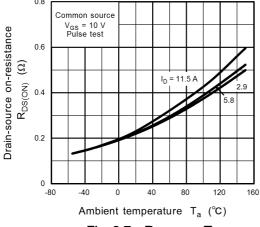


Fig. 8.7 R_{DS(ON)} - T_a

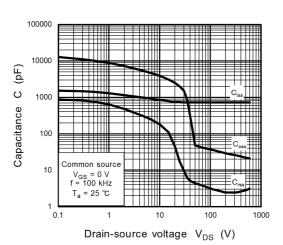


Fig. 8.9 C - V_{DS}

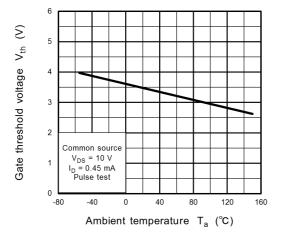


Fig. 8.11 V_{th} - T_a

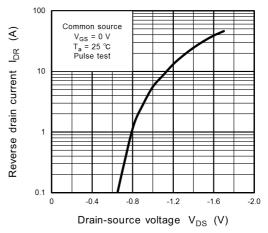


Fig. 8.8 IDR - VDS

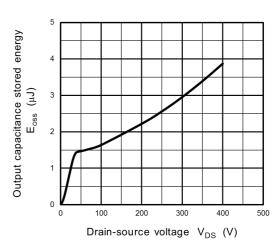


Fig. 8.10 Eoss - VDS

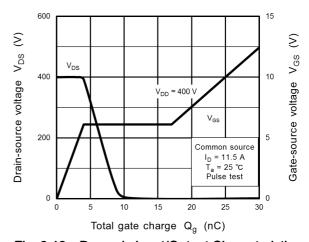


Fig. 8.12 Dynamic Input/Output Characteristics

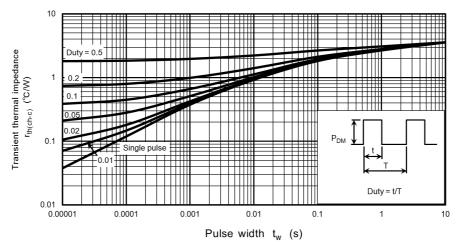


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

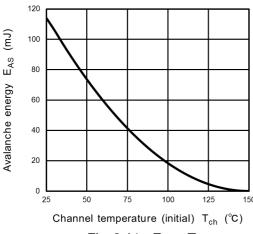


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

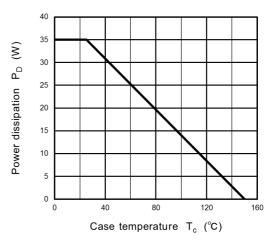
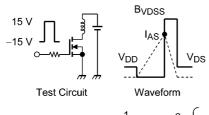


Fig. 8.15 P_D - T_c (Guaranteed Maximum)



 $R_G = 25 \Omega$, $V_{DD} = 90 V$ $E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}}\right)$

Fig. 8.16 Test Circuit/Waveform

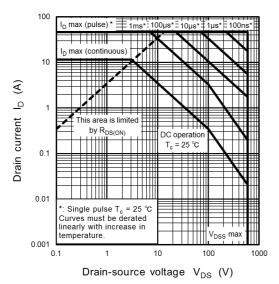


Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

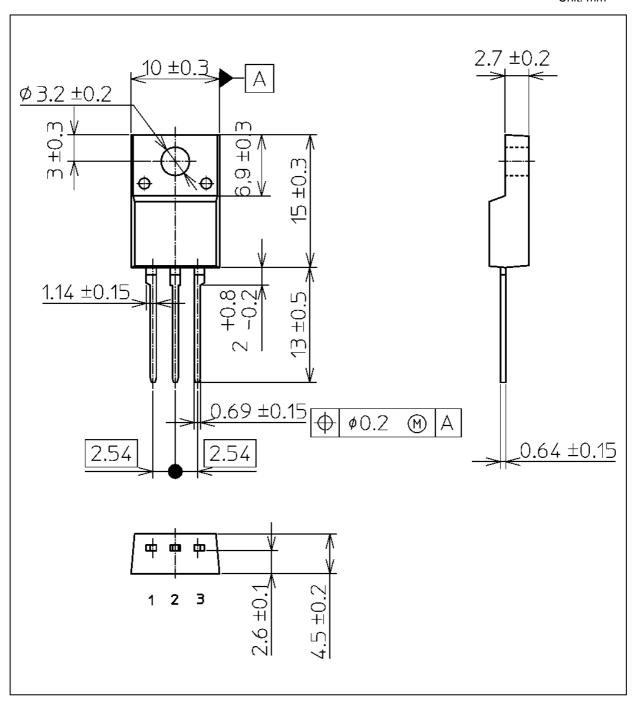
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Rev.2.0



Package Dimensions

Unit: mm



Weight: 1.7 g (typ.)

| | Package Name(s) |
|---------------------|-----------------|
| JEITA: SC-67 | |
| TOSHIBA: 2-10U1S | |
| Nickname: TO-220SIS | |

Rev.2.0



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